



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_C = +25^\circ C$
30V	2.2m Ω @ $V_{GS} = 10V$	170A
	3.2m Ω @ $V_{GS} = 4.5V$	140A

Description and Applications

This new generation MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

- DC-DC Converters
- Load Switch

Features

- Thermally Efficient Package-Cooler Running Applications
- <1.1mm Package Profile – Ideal for Thin Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed

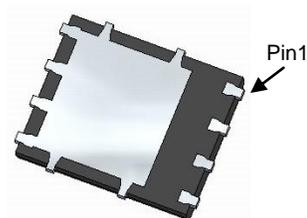
Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)

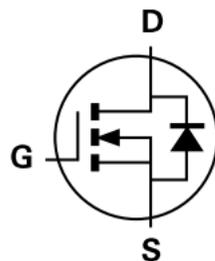
PowerDI5060-8



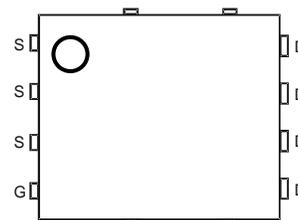
Top View



Bottom View



Internal Schematic


 Top View
 Pin Configuration

Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±16	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	I _D	170	A
Steady State T _C = +25°C T _C = +100°C		120	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	350	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	350	A
Avalanche Current, L = 0.1mH	I _{AS}	50	A
Avalanche Energy, L = 0.1mH	E _{AS}	140	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) T _A = +25°C	P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	54	°C/W
Total Power Dissipation (Note 6) T _C = +25°C	P _D	100	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.6	2.2	mΩ	V _{GS} = 10V, I _D = 30A
		—	2.6	3.2		V _{GS} = 4.5V, I _D = 30A
Diode Forward Voltage	V _{SD}	—	0.8	1.1	V	V _{GS} = 0V, I _S = 30A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	3944	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	1267	—		
Reverse Transfer Capacitance	C _{RSS}	—	186	—		
Gate Resistance	R _g	—	0.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	34	—	nC	V _{DS} = 15V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	68	—		
Gate-Source Charge	Q _{gs}	—	8	—		
Gate-Drain Charge	Q _{gd}	—	15	—		
Turn-On Delay Time	t _{D(ON)}	—	7.2	—	ns	V _{DD} = 15V, V _{GS} = 10V, I _D = 15A, R _G = 3Ω
Turn-On Rise Time	t _R	—	13.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	37.5	—		
Turn-Off Fall Time	t _F	—	23.9	—		
Body Diode Reverse Recovery Time	t _{RR}	—	28.7	—	ns	I _S = 15A, di/dt = 500A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	45.8	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

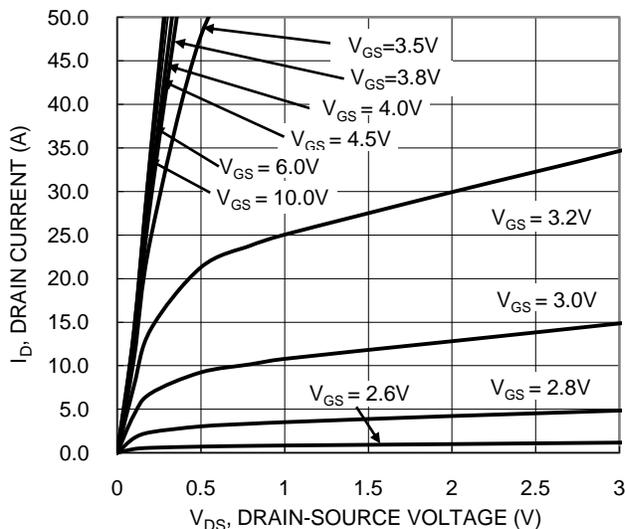


Figure 1. Typical Output Characteristic

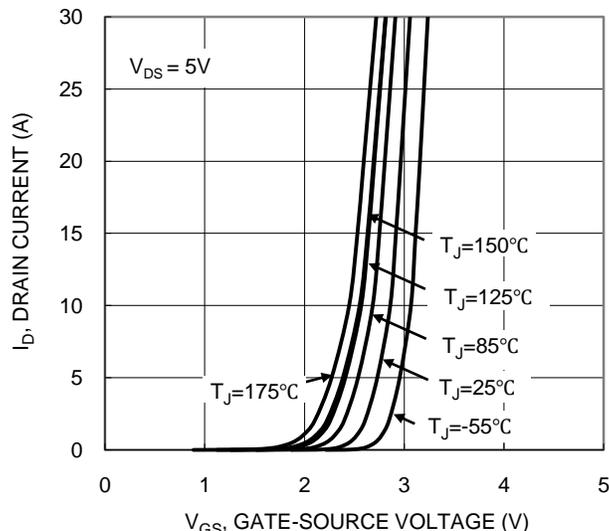


Figure 2. Typical Transfer Characteristic

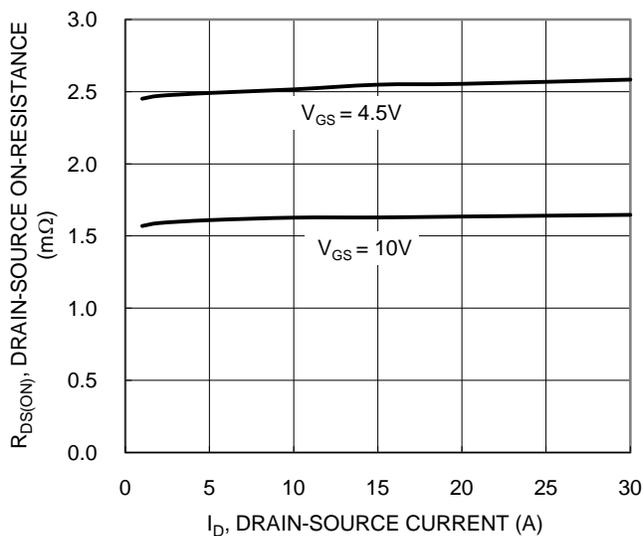


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

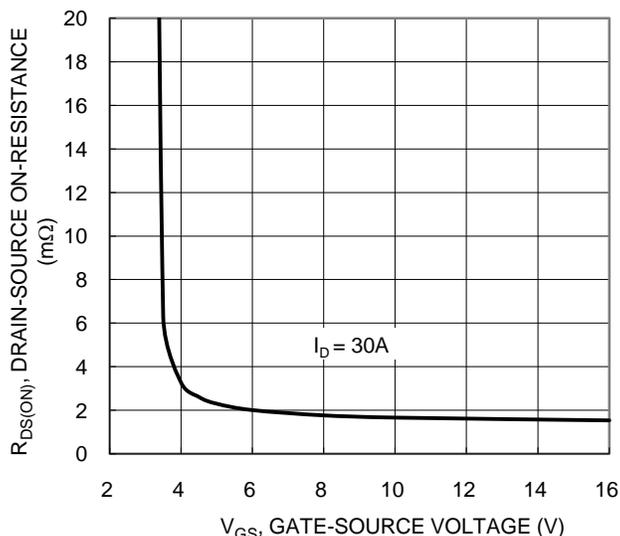


Figure 4. Typical Transfer Characteristic

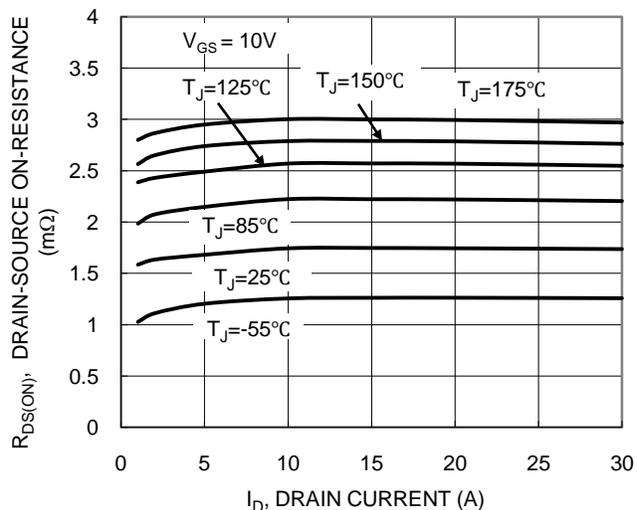


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

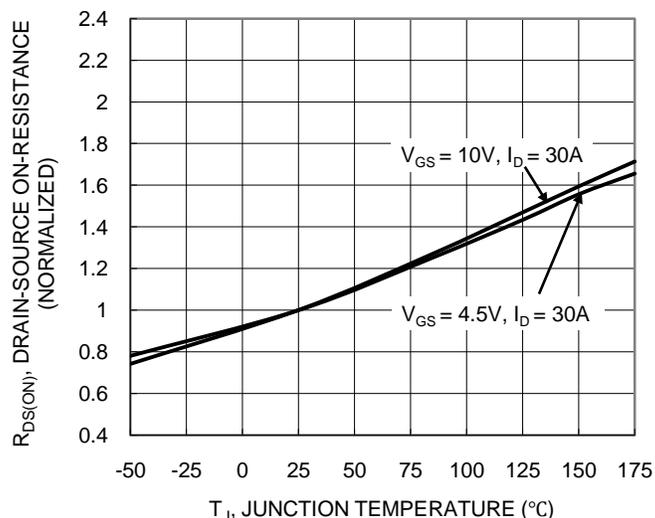


Figure 6. On-Resistance Variation with Temperature

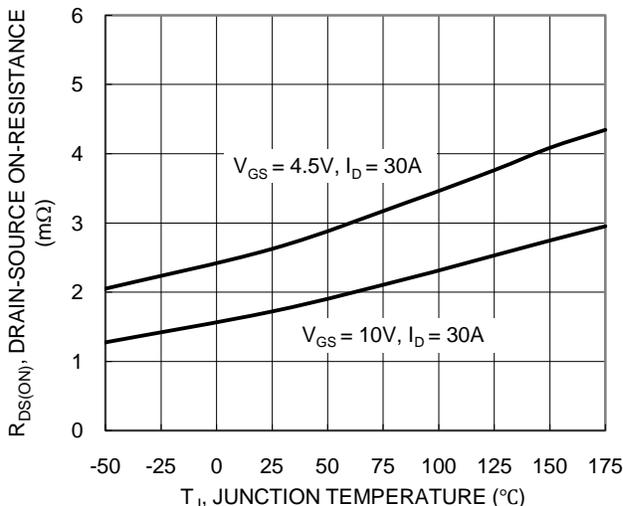


Figure 7. On-Resistance Variation with Temperature

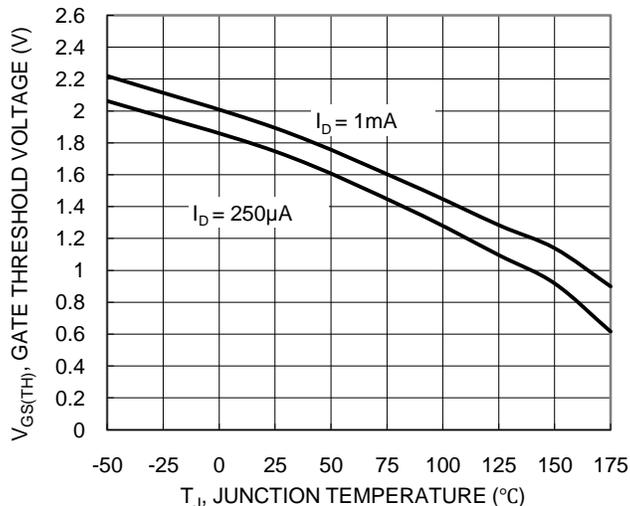


Figure 8. Gate Threshold Variation vs. Junction Temperature

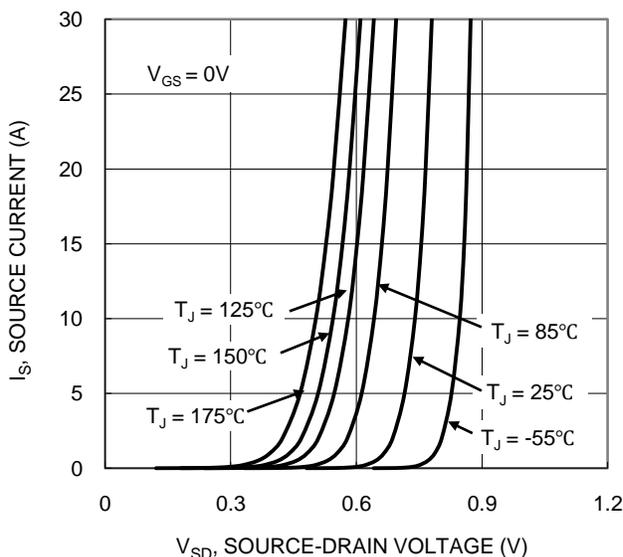


Figure 9. Diode Forward Voltage vs. Current

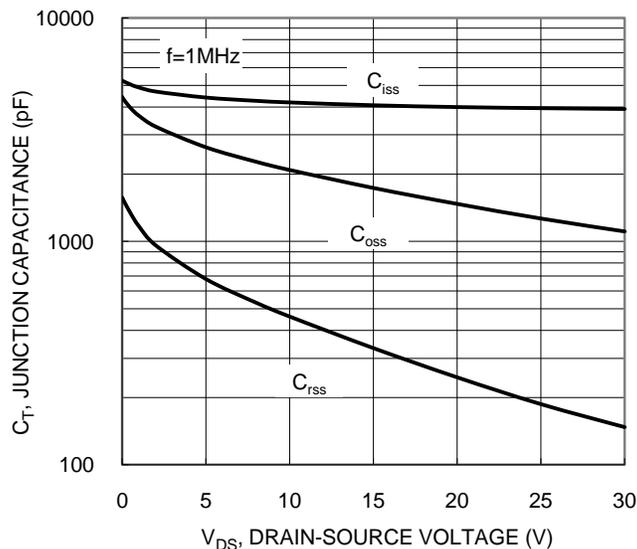


Figure 10. Typical Junction Capacitance

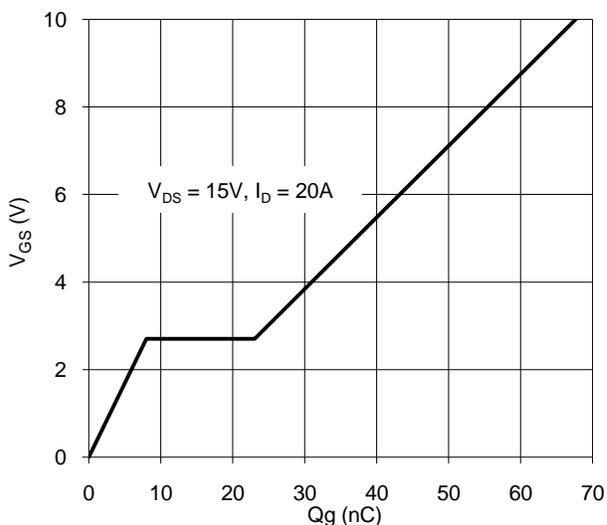


Figure 11. Gate Charge

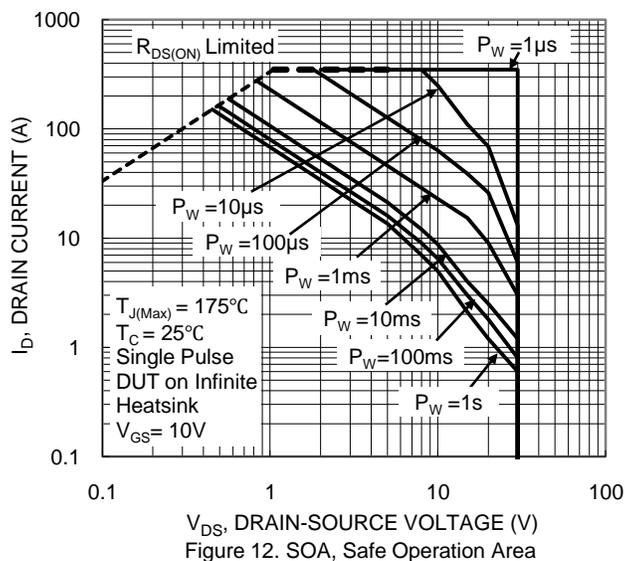


Figure 12. SOA, Safe Operation Area

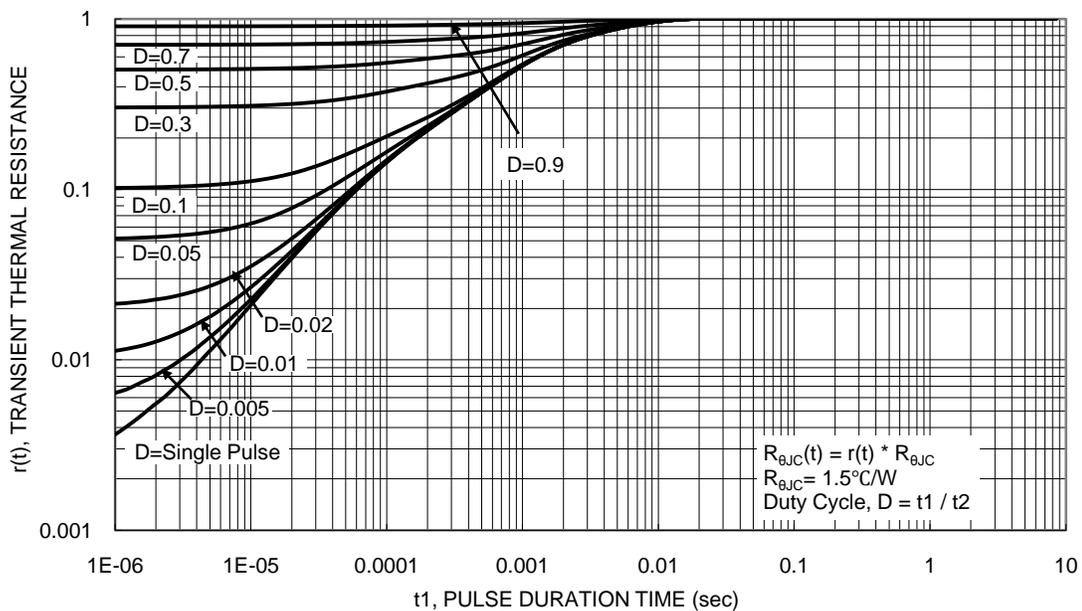
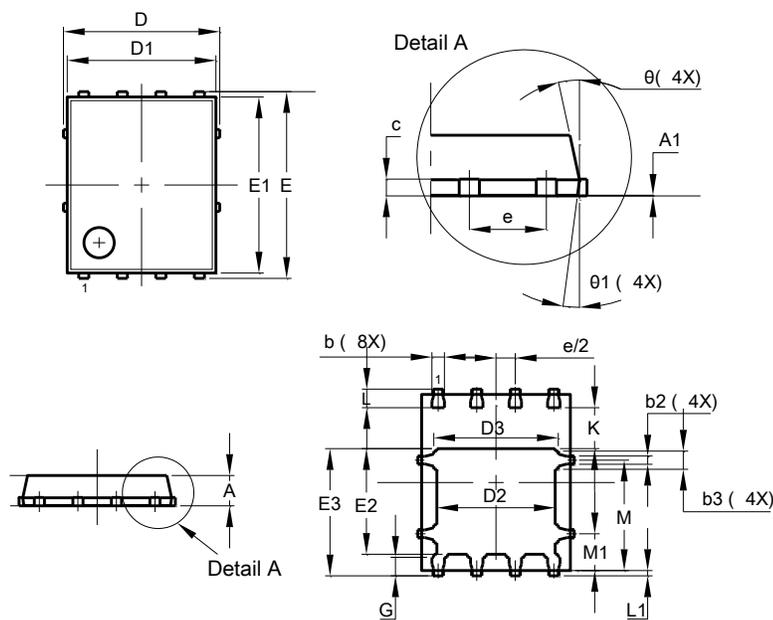


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

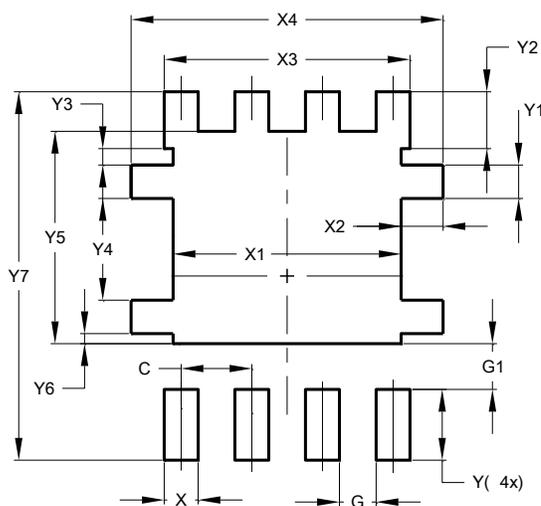
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610